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Attorney's Docket No. 10417-102001

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Previously Presented) A method of manufacturing a circuit device comprising:
preparing a conductive foil and forming an isolation trench having a smaller thickness than that of the conductive foil in the conductive foil, thereby forming a conductive pattern of a first layer;
forming an interlayer insulating film over the conductive pattern of the first layer;
forming plural layers of a conductive pattern on the conductive pattern of the first layer through the interlayer insulating film;
mounting at least one circuit element onto the conductive pattern;
covering the circuit element and entirely molding with an insulating resin; and
removing the conductive foil in a portion where the isolation trench is not formed.
2. (Previously Presented) A method of manufacturing a circuit device according to claim 1 further comprising:
separating the insulating resin through dicing for each circuit device including the circuit element.
3. (Original) The method of manufacturing a circuit device according to claim 1, wherein the conductive foil is constituted by any of copper, aluminum and iron-nickel.
4. (Previously Presented) The method of manufacturing a circuit device according to claim 1, wherein the isolation trench is selectively formed in the conductive foil by chemical or physical etching.

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5. (Original) The method of manufacturing a circuit device according to claim 1, wherein a thermosetting resin is used for the interlayer insulating film.

6. (Previously Presented) The method of manufacturing a circuit device according to claim 5, wherein a via hole is formed in the interlayer insulating film by a laser.

7. (Original) The method of manufacturing a circuit device according to claim 1, wherein a photosensitive resist layer is used for the interlayer insulating film.

8. (Original) The method of manufacturing a circuit device according to claim 7, wherein a via hole is formed on the interlayer insulating film through photosensitization.

9. (Original) The method of manufacturing a circuit device according to claim 1, wherein the conductive pattern of the layers is formed by a copper plated layer.

10. (Original) The method of manufacturing a circuit device according to claim 9, wherein the copper plated layer is formed by electroless plating and electroplating.

11. (Previously Presented) The method of manufacturing a circuit device according to claim 1, wherein the circuit element comprises at least one of a semiconductor bare chip and a chip circuit component.

12. (Original) The method of manufacturing a circuit device according to claim 1, wherein the insulating resin is molded by transfer molding or potting.

13. (Currently Amended) A method of manufacturing a circuit device comprising:

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preparing a conductive foil and forming an isolation trench in the conductive foil thereby forming a conductive pattern;

providing an interlayer insulating film pattern over the conductive foil;

providing plural ~~layers~~ layers of a conductive patterns over the interlayer insulating film pattern;

mounting at least one circuit element onto at least one of the plural layers of the conductive patterns;

covering the circuit element and molding a whole surface with an insulating resin; and removing the conductive foil in a portion where the isolation trench is not formed.

14. (Previously Presented) A method of manufacturing a circuit device according to claim 13 further comprising:

isolating the insulating resin through dicing for each circuit device including the circuit element.

15. (Original) The method of manufacturing a circuit device according to claim 13, wherein the conductive foil is constituted by any of copper, aluminum and iron-nickel.

16. (Original) The method of manufacturing a circuit device according to claim 13, wherein a thermosetting resin is used for the interlayer insulating film.

17. (Original) The method of manufacturing a circuit device according to claim 16, wherein a via hole is formed on the interlayer insulating film through a laser.

18. (Original) The method of manufacturing a circuit device according to claim 13, wherein a photosensitive resist layer is used for the interlayer insulating film.

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19. (Original) The method of manufacturing a circuit device according to claim 18, wherein a via hole is formed on the interlayer insulating film through photosensitization.

20. (Original) The method of manufacturing a circuit device according to claim 13, wherein the conductive pattern of the layers is formed by a copper plated layer.

21. (Original) The method of manufacturing a circuit device according to claim 20, wherein the copper plated layer is formed by electroless plating and electroplating.

22. (Previously Presented) The method of manufacturing a circuit device according to claim 13, wherein the circuit element comprises at least one of a semiconductor bare chip and a chip circuit component.

23. (Original) The method of manufacturing a circuit device according to claim 13, wherein the insulating resin is molded by transfer molding or potting.

24. (Previously Presented) The method of manufacturing a circuit device according to claim 1, wherein a thickness of said conductive foil is 70 to 300 μm .

25. (Previously Presented) The method of manufacturing a circuit device according to claim 13, wherein a thickness of said conductive foil is 70 to 300 μm .

26. (Previously Presented) The method of manufacturing a circuit device according to claim 1, wherein the circuit element is a face down semiconductor element.

27. (Previously Presented) The method of manufacturing a circuit device according to claim 13, wherein the circuit element is a face down semiconductor element.